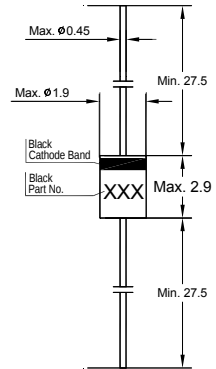


SB721Q-40

Silicon Epitaxial Planar Schottky Barrier Diode

Applications

- High speed switching



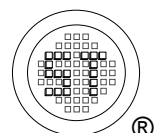
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	30	mA
Peak Forward Surge Current	I_{FSM}	200	mA
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	-	0.37	V
Reverse Current at $V_R = 25\text{ V}$	I_R	-	-	0.5	μA
Reverse Voltage at $I_R = 10\text{ }\mu\text{A}$	V_R	40	-	-	V
Capacitance between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	-	2	-	pF



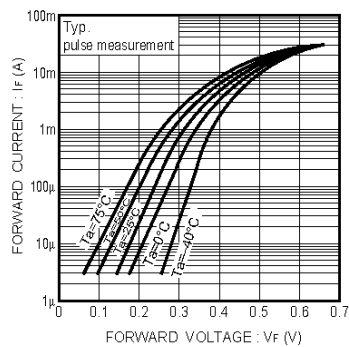


Fig.1 Forward characteristics

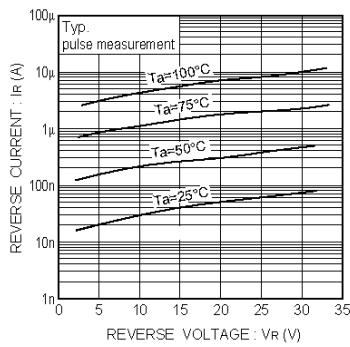


Fig.2 Reverse characteristics

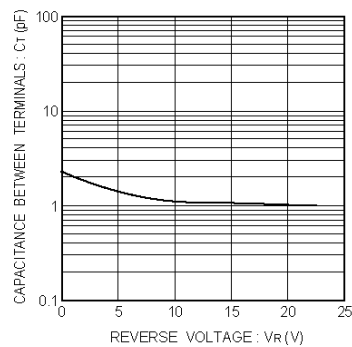


Fig.3 Capacitance between terminals characteristics

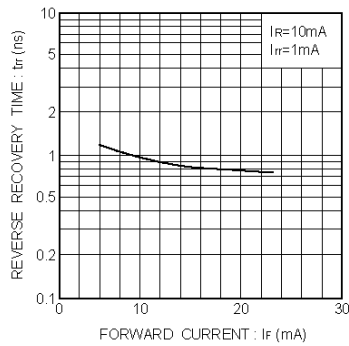


Fig.4 Reverse recovery time characteristics

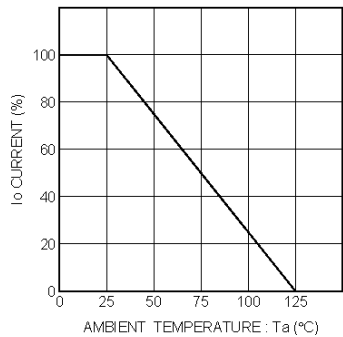


Fig.5 Derating curve (mounting on glass epoxy PCBs)

